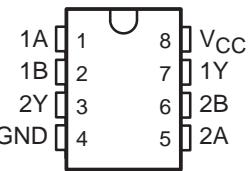


- **EPIC™ (Enhanced-Performance Implanted CMOS) Process**
- **I_{off} Feature Supports Partial-Power-Down Mode Operation**
- **Supports 5-V V_{CC} Operation**
- **Package Options Include Plastic Thin Shrink Small-Outline (DCT, DCU) Packages**

DCT OR DCU PACKAGE
(TOP VIEW)



description

This dual 2-input positive-NAND gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G00 performs the Boolean function $Y = \overline{A} \bullet \overline{B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

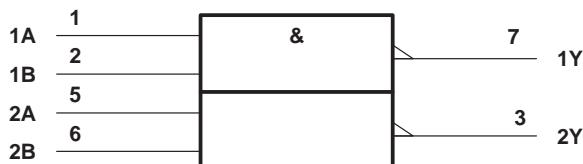
This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC2G00 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE
(each gate)

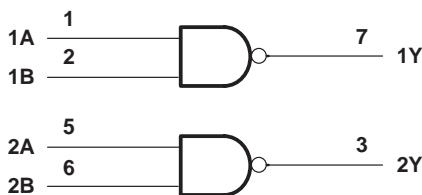
| INPUTS | | OUTPUT |
|--------|---|--------|
| A | B | Y |
| H | H | L |
| L | X | H |
| X | L | H |

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC is a trademark of Texas Instruments Incorporated.

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.

Copyright © 2000, Texas Instruments Incorporated

SN74LVC2G00

DUAL 2-INPUT POSITIVE-NAND GATE

SCES193B – APRIL 1999 – REVISED FEBRUARY 2000

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

| | |
|--|----------------------------|
| Supply voltage range, V_{CC} | –0.5 V to 6.5 V |
| Input voltage range, V_I (see Note 1) | –0.5 V to 6.5 V |
| Output voltage range, V_O (see Notes 1 and 2) | –0.5 V to V_{CC} + 0.5 V |
| Input clamp current, I_{IK} ($V_I < 0$) | –50 mA |
| Output clamp current, I_{OK} ($V_O < 0$) | –50 mA |
| Continuous output current, I_O | ±50 mA |
| Continuous current through V_{CC} or GND | ±100 mA |
| Package thermal impedance, θ_{JA} (see Note 3): DCT package | 296°C/W |
| DCU package | 329°C/W |
| Storage temperature range, T_{STG} | –65°C to 150°C |

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 2. The value of V_{CC} is provided in the recommended operating conditions table.
 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

| | | | MIN | MAX | UNIT |
|---------------------|------------------------------------|--|-----------------|-----|------|
| V_{CC} | Supply voltage | Operating | 1.65 | 5.5 | V |
| | | Data retention only | 1.5 | | |
| V_{IH} | High-level input voltage | $V_{CC} = 1.65$ V to 1.95 V | 0.65 × V_{CC} | | V |
| | | $V_{CC} = 2.3$ V to 2.7 V | 1.7 | | |
| | | $V_{CC} = 3$ V to 3.6 V | 2 | | |
| | | $V_{CC} = 4.5$ V to 5.5 V | 0.7 × V_{CC} | | |
| V_{IL} | Low-level input voltage | $V_{CC} = 1.65$ V to 1.95 V | 0.35 × V_{CC} | | V |
| | | $V_{CC} = 2.3$ V to 2.7 V | 0.7 | | |
| | | $V_{CC} = 3$ V to 3.6 V | 0.8 | | |
| | | $V_{CC} = 4.5$ V to 5.5 V | 0.3 × V_{CC} | | |
| V_I | Input voltage | 0 | 5.5 | V | |
| V_O | Output voltage | 0 | V_{CC} | V | |
| I_{OH} | High-level output current | $V_{CC} = 1.65$ V | –4 | | mA |
| | | $V_{CC} = 2.3$ V | –8 | | |
| | | $V_{CC} = 3$ V | –16 | | |
| | | | –24 | | |
| | | $V_{CC} = 4.5$ V | –32 | | |
| I_{OL} | Low-level output current | $V_{CC} = 1.65$ V | 4 | | mA |
| | | $V_{CC} = 2.3$ V | 8 | | |
| | | $V_{CC} = 3$ V | 16 | | |
| | | | 24 | | |
| | | $V_{CC} = 4.5$ V | 32 | | |
| $\Delta t/\Delta v$ | Input transition rise or fall rate | $V_{CC} = 1.8$ V ± 0.15 V, 2.5 V ± 0.2 V | 20 | | ns/V |
| | | $V_{CC} = 3.3$ V ± 0.3 V | 10 | | |
| | | $V_{CC} = 5$ V ± 0.5 V | 5 | | |
| TA | Operating free-air temperature | –40 | 85 | °C | |

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | V _{CC} | MIN | TYP [†] | MAX | UNIT |
|------------------|--|-------------------------------|----------------------|------------------|-----|------|
| V _{OH} | I _{OH} = -100 µA | 1.65 V to 5.5 V | V _{CC} –0.1 | | | V |
| | I _{OH} = -4 mA | 1.65 V | 1.2 | | | |
| | I _{OH} = -8 mA | 2.3 V | 1.9 | | | |
| | I _{OH} = -16 mA | | 2.4 | | | |
| | I _{OH} = -24 mA | 3 V | 2.3 | | | |
| | I _{OH} = -32 mA | 4.5 V | 3.8 | | | |
| V _{OL} | I _{OL} = 100 µA | 1.65 V to 5.5 V | | 0.1 | | V |
| | I _{OL} = 4 mA | 1.65 V | | 0.45 | | |
| | I _{OL} = 8 mA | 2.3 V | | 0.3 | | |
| | I _{OL} = 16 mA | | 0.4 | | | |
| | I _{OL} = 24 mA | 3 V | | 0.55 | | |
| | I _{OL} = 32 mA | 4.5 V | | 0.55 | | |
| I _I | A or B inputs | V _I = 5.5 V or GND | 0 to 5.5 V | | ±5 | µA |
| I _{off} | V _I or V _O = 5.5 V | | 0 | | ±10 | µA |
| I _{CC} | V _I = 5.5 V or GND, I _O = 0 | 1.65 V to 5.5 V | | 10 | | µA |
| ΔI _{CC} | One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND | 3 V to 5.5 V | | 500 | | µA |
| C _i | V _I = V _{CC} or GND | 3.3 V | | | | pF |

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | V _{CC} = 1.8 V ± 0.15 V | V _{CC} = 2.5 V ± 0.2 V | V _{CC} = 3.3 V ± 0.3 V | V _{CC} = 5 V ± 0.5 V | UNIT |
|-----------------|-----------------|----------------|-------------------------------------|------------------------------------|------------------------------------|----------------------------------|------|
| | | | MIN | MAX | MIN | MAX | |
| t _{pd} | A or B | Y | | | | | ns |

operating characteristics, T_A = 25°C

| PARAMETER | TEST CONDITIONS | V _{CC} = 1.8 V | V _{CC} = 2.5 V | V _{CC} = 3.3 V | V _{CC} = 5 V | UNIT |
|---|-----------------|-------------------------|-------------------------|-------------------------|-----------------------|------|
| | | MIN | MAX | MIN | MAX | |
| C _{pd} Power dissipation capacitance | f = 10 MHz | | | | | pF |

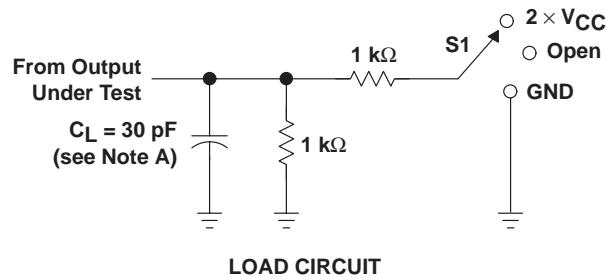
SN74LVC2G00

DUAL 2-INPUT POSITIVE-NAND GATE

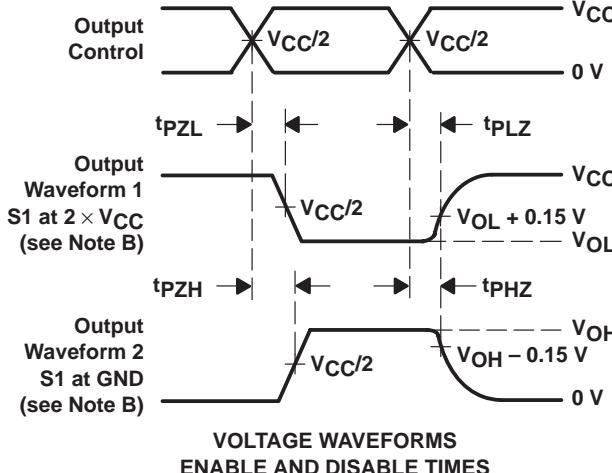
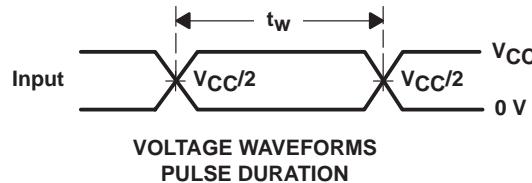
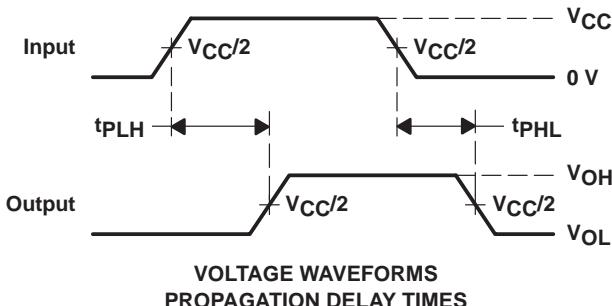
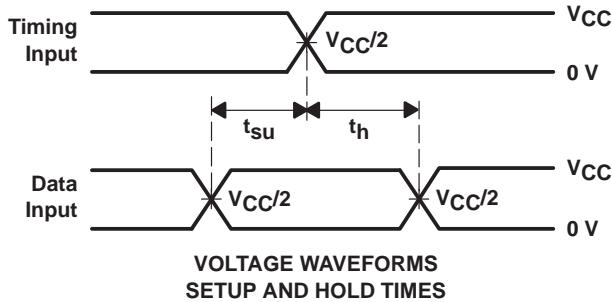
SCES193B – APRIL 1999 – REVISED FEBRUARY 2000

PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$$



| TEST | S1 |
|-------------------|-------------------|
| t_{pd} | Open |
| t_{PLZ}/t_{PZL} | $2 \times V_{CC}$ |
| t_{PHZ}/t_{PZH} | GND |

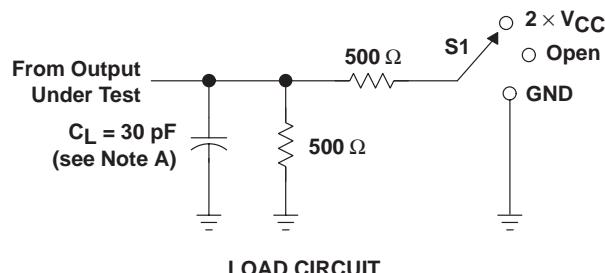


NOTES:

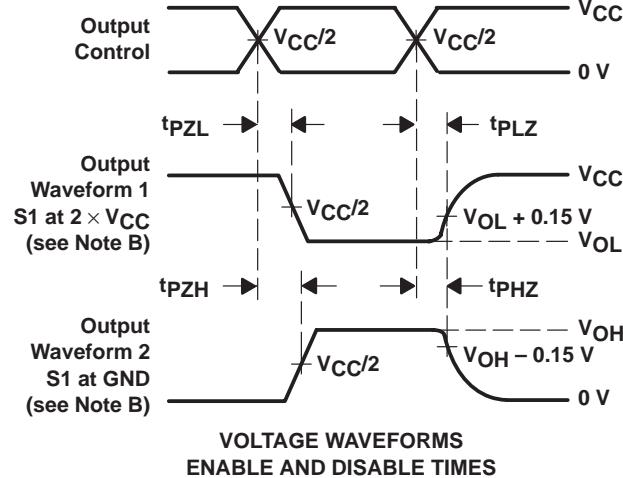
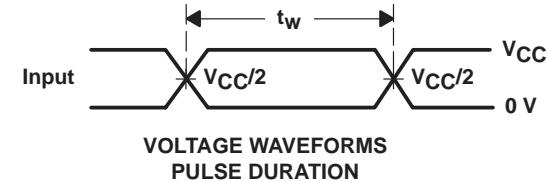
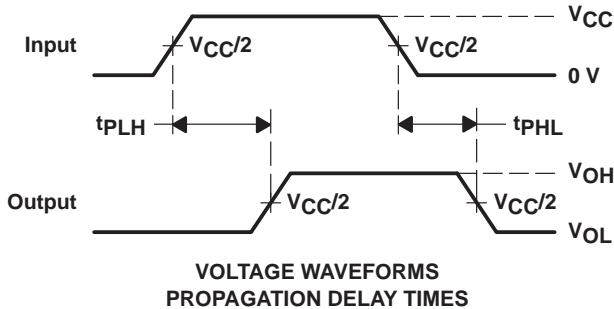
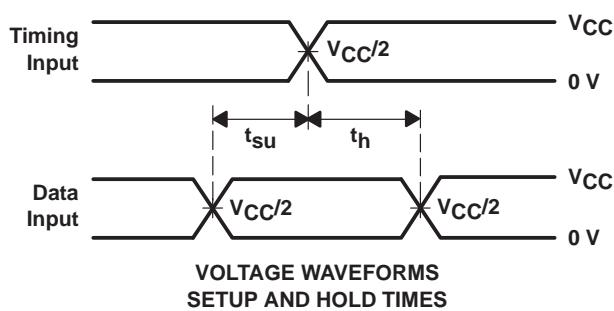
- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
- The outputs are measured one at a time with one transition per measurement.
- t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- t_{PZL} and t_{PZH} are the same as t_{en} .
- t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
 $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



| TEST | S1 |
|-------------------|---------|
| t_{pd} | Open |
| t_{PLZ}/t_{PZL} | 2 × VCC |
| t_{PHZ}/t_{PZH} | GND |



NOTES:

- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
- The outputs are measured one at a time with one transition per measurement.
- t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- t_{PZL} and t_{PZH} are the same as t_{en} .
- t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

SN74LVC2G00

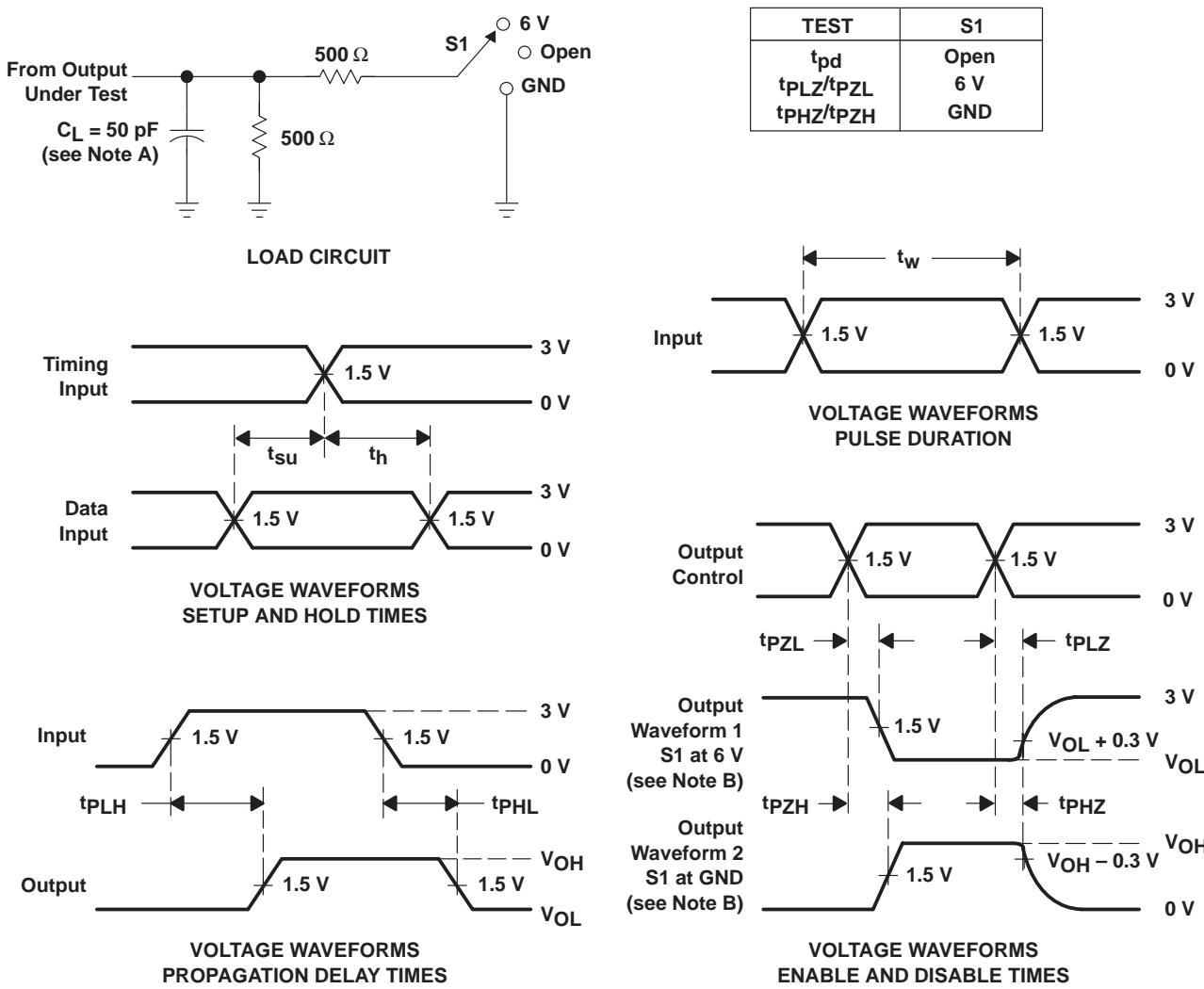
DUAL 2-INPUT POSITIVE-NAND GATE

SCES193B – APRIL 1999 – REVISED FEBRUARY 2000

PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$

PRODUCT PREVIEW

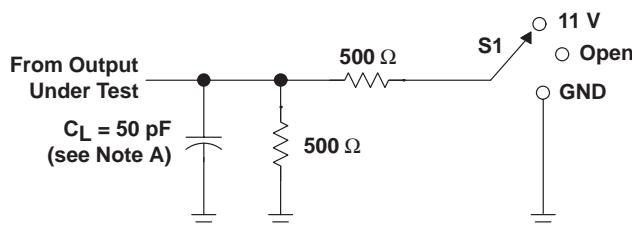


NOTES:

- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
- The outputs are measured one at a time with one transition per measurement.
- t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- t_{PZL} and t_{PZH} are the same as t_{en} .
- t_{PLH} and t_{PHL} are the same as t_{pd} .

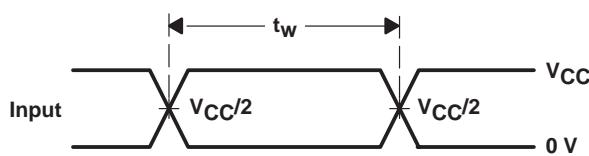
Figure 3. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
 $V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$

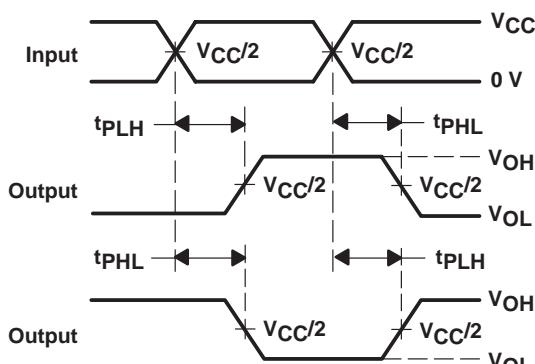


| TEST | S1 |
|-------------------|------|
| t_{PLH}/t_{PHL} | Open |
| t_{PLZ}/t_{PZL} | 11 V |
| t_{PHZ}/t_{PZH} | GND |

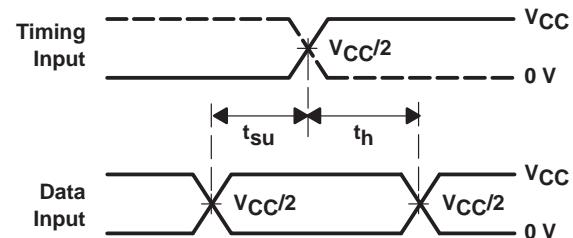
LOAD CIRCUIT



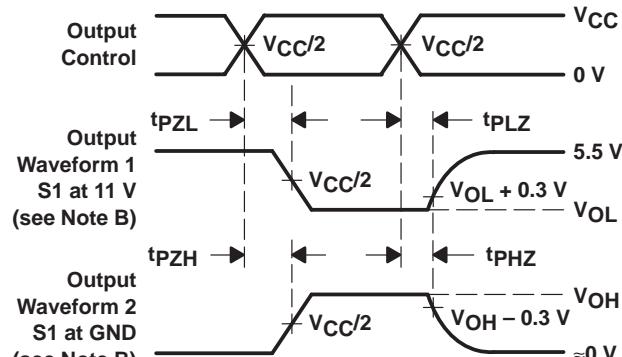
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES:

- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
- The outputs are measured one at a time with one transition per measurement.
- t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- t_{PZL} and t_{PZH} are the same as t_{en} .
- t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 4. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated